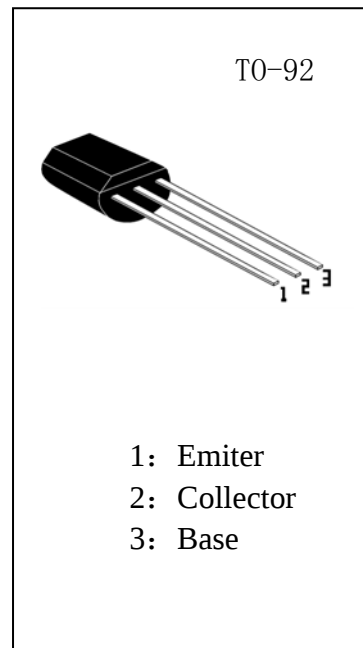


大电流低压晶体管

- 电流输出最大达 3A
- 低饱和电压
- 与 2SD882 对管

极限参数(Absolute Maximum Ratings) Ta=25°C

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	Vcbo	-40	V
Collector-Emitter Voltage	Vceo	-30	V
Emitter-Base Voltage	Vebo	-5	V
Collector Current (DC)	Ic	-3	A
Collector Current (PLUSE)	Ic	-7	A
Base current	Ib	-0.6	A
Collector Dissipation	Pc	750	mW
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55~150	°C



电性能(Electrical Characteristic) Ta=25°C

Symbol	Characteristic	Test Condition	Min	Typ	Max	Unit
BVcbo	Collector-Base Breakdown Voltage	Ic=-100uA Ie=0	-40			V
BVceo	Collector-Emitter Breakdown Voltage	Ic=-1mA Ib=0	-30			V
BVebo	Emitter-Base Breakdown Voltage	Ie=-100uA Ic=0	-5			V
Icbo	Collector Cutoff Current	Vcb=-30V, Ie=0			-1	uA
Iebo	Emitter Cutoff Current	Veb=-3V, Ic=0			-1	uA
Iceo	Collector Cutoff Current	Vce=-20V, Ib=0			-10	uA
Vce(sat)	Collector-Emitter Saturation Voltage	Ic=-2A, Ib=-0.2A		-0.3	-0.5	V
Vbe(sat)	Base-Emitter Saturation Voltage	Ic=-2A, Ib=-0.2A		-1	-2	V
Hfe1	DC Current Gain	Vce=-2V, Ic=-20mA	30			
Hfe2	DC Current Gain	Vce=-2V, Ic=-1A	100		400	
Cob	Output Capacitance	Vcb=-10V, Ie=0, f=1MHz		45		PF
fT	Current Gain-Bandwidth product	Vce=-5V, Ic=-0.1A	80			MHz

Class	Q	P	E
Hfe2	100-160	160-320	320-400